



**ALPHA & OMEGA**  
SEMICONDUCTOR

# ***AOS Semiconductor Product Reliability Report***

**AOBS30B65LN**, rev A

**Plastic Encapsulated Device**

**ALPHA & OMEGA Semiconductor, Inc**

**[www.aosmd.com](http://www.aosmd.com)**

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This AOS product reliability report summarizes the qualification result for AOBS30B65LN. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AOBS30B65LN passes AOS quality and reliability requirements. The released product will be categorized by the process family and be routine monitored for continuously improving the product quality.

## I. Reliability Stress Test Summary and Results

Test Item	Test Condition	Time Point	Total Sample Size	Number of Failures	Reference Standard
HTGB	Temp = 175°C , Vge=100% of Vgemax	168 / 500 / 1000 hours	462 pcs	0	JESD22-A108
HTRB	Temp = 175°C , Vce=100% of Vcemax	168 / 500 / 1000 hours	462 pcs	0	JESD22-A108
Precondition (Note A)	168hr 85°C / 85%RH + 3 cycle reflow @245°C (MSL 1)	-	4620 pcs	0	JESD22-A113
HAST	130°C , 85%RH, 33.3 psia, Vce = 80% of Vcemax up to 42V	96 hours	693 pcs	0	JESD22-A110
H3TRB	85°C , 85%RH, Vce = 80% of Vcemax up to 100V	1000 hours	693 pcs	0	JESD22-A101
Autoclave	121°C , 29.7psia, RH=100%	96 hours	924 pcs	0	JESD22-A102
Temperature Cycle	-65°C to 150°C , air to air,	1000 cycles	924 pcs	0	JESD22-A104
HTSL	Temp = 175°C	1000 hours	693 pcs	0	JESD22-A103
IOL	Δ Tj = 100°C	8572 cycles	693 pcs	0	MIL-STD-750 Method 1037

**Note:** The reliability data presents total of available generic data up to the published date.

Note A: MSL (Moisture Sensitivity Level) 1 based on J-STD-020

## II. Reliability Evaluation

**FIT rate (per billion): 3.82**

**MTTF = 29919 years**

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size. Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

**Failure Rate** =  $\text{Chi}^2 \times 10^9 / [2 (N) (H) (Af)] = 3.82$

**MTTF** =  $10^9 / \text{FIT} = 29919$  years

**Chi<sup>2</sup>** = Chi Squared Distribution, determined by the number of failures and confidence interval

**N** = Total Number of units from burn-in tests

**H** = Duration of burn-in testing

**Af** = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor **[Af]** =  $\text{Exp} [Ea / k (1/Tj u - 1/Tj s)]$

**Acceleration Factor ratio list:**

	55 deg C	70 deg C	85 deg C	100 deg C	125 deg C	150 deg C	175 deg C
<b>Af</b>	<b>758</b>	<b>256</b>	<b>95</b>	<b>38</b>	<b>9.7</b>	<b>2.9</b>	<b>1</b>

**Tj s** = Stressed junction temperature in degree (Kelvin), K = C+273.16

**Tj u** = The use junction temperature in degree (Kelvin), K = C+273.16

**k** = Boltzmann's constant,  $8.617164 \times 10^{-5} \text{eV} / \text{K}$